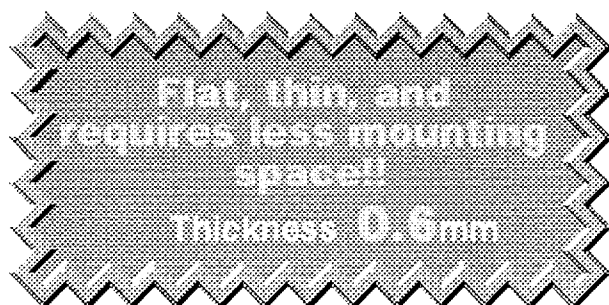
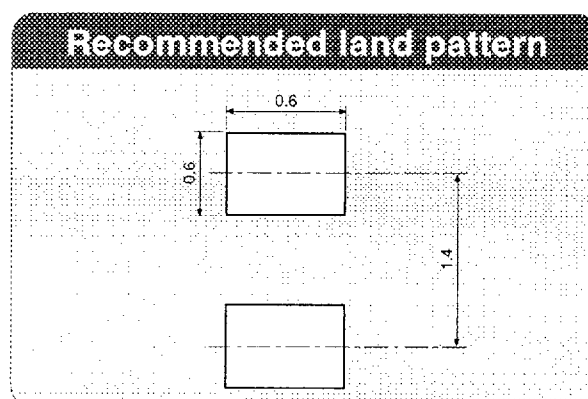
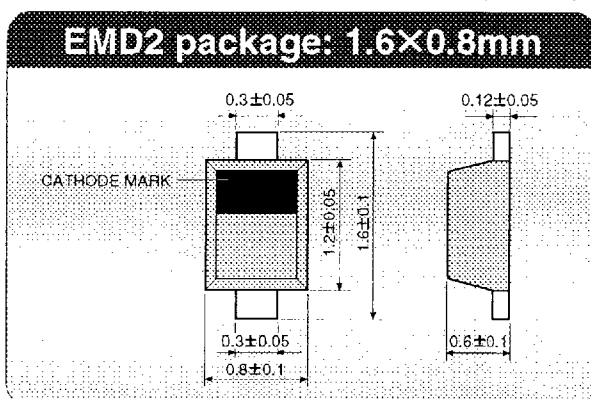


EMD2(1208)size

ROHM is a semiconductor manufacturer and has a series of the world's smallest packages!



Surface Mounted package
Extremely popular for
portable products Double-terminal
Diodes You can make
your products lighter
and smaller with it!



Type. No.	Application
1SS390	Band Switching
1SS400	0.1A/80V General Switching
RB520S-30	0.2A/30V Low IR Schottky
RB521S-30	0.2A/30V Low VF Schottky
RB751S-40	30mA/40V Detection Schottky
EDZ[] Bseries	Voltage: 4.7V~6.8V

Band switching diode (Silicon Epitaxial Planer)

1SS390

APPLICATION

High frequency Switching

FEATURE

- Ultra small mold type (EMD2)
- High reliability

ABSOLUTE MAXIMUM RATING(Ta=25°C)

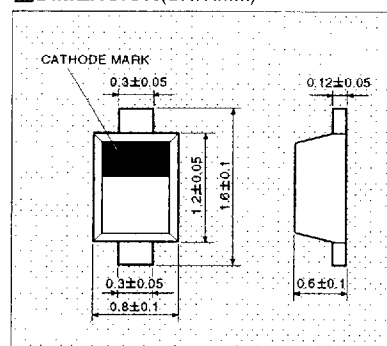
Characteristic	Symbol	Limits
Forward current(DC)	IF	100mA
Reverse voltage(DC)	VR	35V
Junction temperature	Tj	125°C
Storage temperature	Tstg	-55~125°C

ELECTRICAL CHARACTERISTIC(Ta=25°C)

Characteristic	Symbol	Test condition	Standard
Forward voltage	VF	IF=10mA	1.0V Max.
Reverse current	IR	VR=25V	10nA Max.
Capacitance between terminal	Cl	VR=6V f=1MHz	1.2pF Max.
Forward operating resistance	rf	IF=2mA f=100MHz RL=100Ω	0.9Ω Max.

*Please pay attention to static electricity when handling.

DIMENSION(UNIT:mm)



Mass per piece
 1.5mg/pcs

Switching diode (Silicon Epitaxial Planer)

1SS400

APPLICATION

High speed switching

FEATURE

- Ultra small mold type (EMD2)
- High reliability

Mass per piece

1.5mg/pcs

ABSOLUTE MAXIMUM RATING(Ta=25°C)

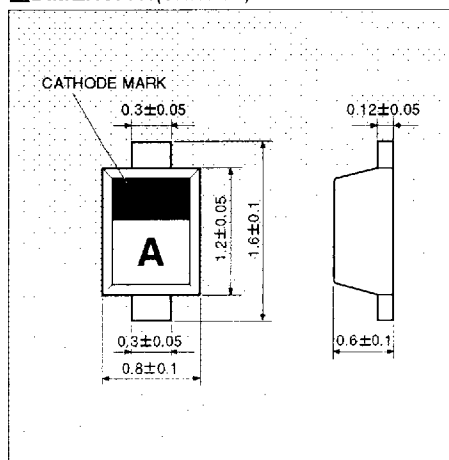
Characteristic	Symbol	Limits
Reverse voltage(repetitive peak)	VRM	90V
Reverse voltage(DC)	VR	80V
Forward current(repetitive peak)	IFM	225mA
Average rectified forward current	Io	100mA
Forward current(DC)	IF	100mA
Surge current(1sec)	Isurge	500mA
Junction temperature	Tj	125°C
Storage temperature	Tstg	-55~125°C

ELECTRICAL CHARACTERISTIC(Ta=25°C)

Characteristic	Symbol	Test condition	Standard
Forward voltage	VF	IF=100mA	1.2V Max.
Reverse current	IR	VR=80V	100nA Max.
Reverse voltage	VR	IF=100μA	90V Min.
Capacitance between terminal	CI	VR=0.5V f=1MHz	3.0pF Max.
Reverse recovery time	trr	VR=6V IF=10mA RL=100Ω	4.0 nS Max.

*Please pay attention to static electricity when handling

DIMENSION(UNIT:mm)



Schottky barrier diode (Silicon Epitaxial Planer)

RB520S-30

Low IR

APPLICATION

High speed switching

FEATURE

- Ultra small mold type (EMD2)
- High reliability

Mass per piece

1.5mg/pcs

ABSOLUTE MAXIMUM RATING(Ta=25°C)

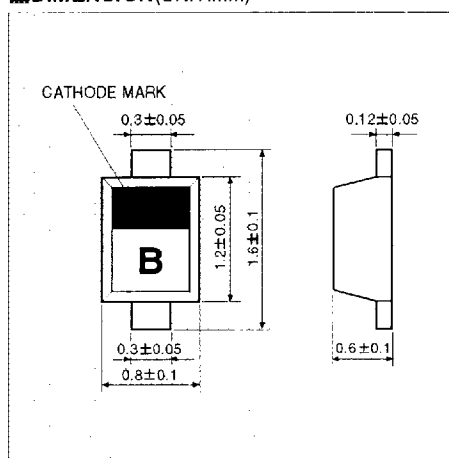
Characteristic	Symbol	Limits
Average rectified forward current	Io	200mA
Reverse voltage(DC)	VR	30V
Junction temperature	Tj	125°C
Storage temperature	Tstg	-40~125°C

ELECTRICAL CHARACTERISTIC(Ta=25°C)

Characteristic	Symbol	Test condition	Standard
Forward voltage	VF	IF=200mA	0.60V Max.
Reverse current	IR	VR=10V	1.0μA Max.

*Please pay attention to static electricity when handling.

DIMENSION(UNIT:mm)



Schottky barrier diode (Silicon Epitaxial Planer)

RB521S-30

Low VF

APPLICATION

High speed switching

FEATURE

- Ultra small mold type (EMD2)
- High reliability

Mass per piece

1.5mg/pcs

ABSOLUTE MAXIMUM RATING(Ta=25°C)

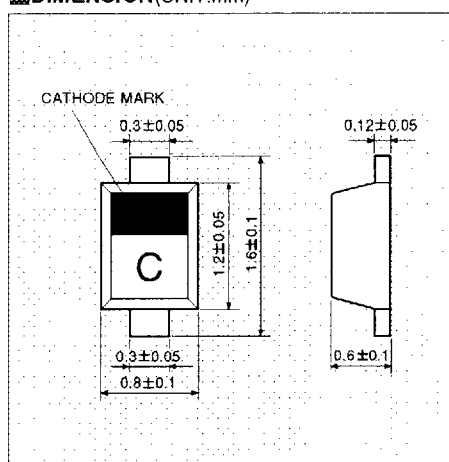
Characteristic	Symbol	Limits
Average rectified forward current	Io	200mA
Reverse voltage(DC)	VR	30V
Junction temperature	Tj	125°C
Storage temperature	Tstg	-40~125°C

ELECTRICAL CHARACTERISTIC(Ta=25°C)

Characteristic	Symbol	Test condition	Standard
Forward voltage	VF	IF=200mA	0.50V Max.
Reverse current	IR	VR=10V	30μA Max.

*Please pay attention to static electricity when handling.

DIMENSION(UNIT:mm)



Schottky barrier diode (Silicon Epitaxial Planer)

RB751S-40

General detection

APPLICATION

High speed switching

FEATURE

- Ultra small mold type (EMD2)
- High reliability

Mass per piece

1.5mg/pcs

ABSOLUTE MAXIMUM RATING(Ta=25°C)

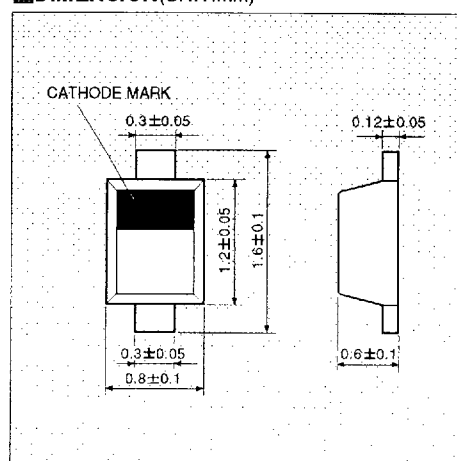
Characteristic	Symbol	Limits
Reverse voltage(repetitive peak)	VRM	40V
Reverse voltage(DC)	VR	30V
Average rectified forward current	Io	30mA
Forward current surge(80Hz,1ms)	IFSM	200mA
Junction temperature	Tj	125°C
Storage temperature	Tstg	-40~125°C

ELECTRICAL CHARACTERISTIC(Ta=25°C)

Characteristic	Symbol	Test condition	Standard
Forward current	VF	IF=1.0mA	0.37V Max.
Reverse current	IR	VR=30V	0.5μA Max.
Capacitance between terminal	Ct	VR=1.0V f=1.0MHz	2.0pF TYP.

*Please pay attention to static electricity when handling.

DIMENSION(UNIT:mm)



Zener diode

EDZ B Series

Low Ct

APPLICATION

Voltage Regulation

FEATURE

- Ultra small mold type (EMD2)
- High reliability
- By chip-mounter, automatic mounting is possible.

Mass per piece

1.5mg/pcs

ABSOLUTE MAXIMUM RATING(Ta=25°C)

Characteristic	Symbol	Limits
Power dissipation	P	100mW
Junction temperature	Tj	125°C
Storage temperature	Tstg	-55~125°C
Operation temperature	Topr	-55~125°C

ELECTRICAL CHARACTERISTIC(Ta=25°C)

Typ. No.	Zener voltage			Dynamic impedance		Dynamic knee impedance		Reverse current	
	Vz(V)			Zzk(Ω)		Zzk(Ω)		IR(μA)	
	Min.	Max.	Iz(mA)	Max.	Iz(mA)	Max.	Iz(mA)	Max.	VR(V)
EDZ 4.7B	4.550	4.750	5	100	5	800	0.5	2	1.0
EDZ 5.1B	4.980	5.200	5	80	5	500	0.5	2	1.5
EDZ 5.6B	5.490	5.730	5	60	5	200	0.5	1	2.5
EDZ 6.2B	6.060	6.330	5	60	5	100	0.5	1.0	3.0
EDZ 6.8B	6.650	6.930	5	40	5	60	0.5	0.5	3.5

(1) Zener voltage(Vz) shall be measured at 40msec after loading current.

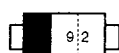
(2) Dynamic resistance(Zz, Zzk) shall be measured by applying very small AC current and specified current(Iz) simultaneously.

*Please pay attention to static electricity when handling.

MARKING(Typ. NO.)

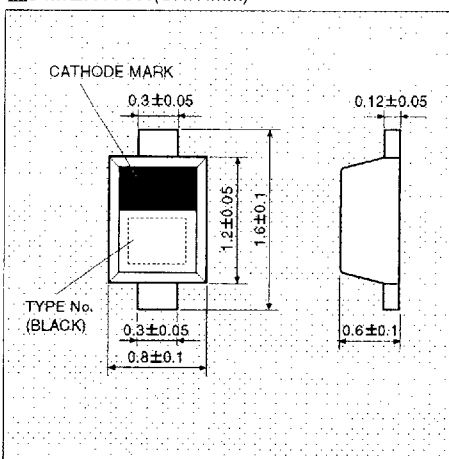
VOLTAGE	TYPE. No.	
EDZ 4.7B	9	2
EDZ 5.1B	A	2
EDZ 5.6B	C	2
EDZ 6.2B	E	2
EDZ 6.8B	F	2

(EX)EDZ 4.7B



First Marking
↓
9
Second Marking
↓
2

DIMENSION(UNIT:mm)



*TYPE No. shows typical value of zener voltage and symbol of voltage classification.